

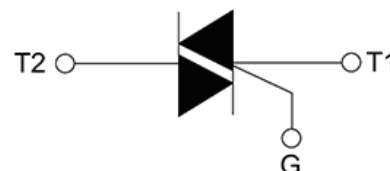
## DESCRIPTION:

The chip triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The chip embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. At the same time, the triac shields the positive signal trigger to reduce the probability of product misoperation. It is triggered with a negative gate current flowing out of the gate pin.



## MAIN FEATURES

| Symbol             | Value    | Unit |
|--------------------|----------|------|
| $I_{T(RMS)}$       | 12       | A    |
| $V_{DRM}/V_{RRM}$  | 800      | V    |
| $I_{GT\ I/II/III}$ | 20/20/20 | mA   |



## ABSOLUTE MAXIMUM RATINGS

| Parameter                                                                                            | Symbol       | Value   | Unit             |
|------------------------------------------------------------------------------------------------------|--------------|---------|------------------|
| Storage junction temperature range                                                                   | $T_{stg}$    | -40-150 | °C               |
| Operating junction temperature range                                                                 | $T_j$        | -40-150 | °C               |
| Repetitive peak off-state voltage ( $T_j=25^{\circ}C$ )                                              | $V_{DRM}$    | 800     | V                |
| Repetitive peak reverse voltage ( $T_j=25^{\circ}C$ )                                                | $V_{RRM}$    | 800     | V                |
| RMS on-state current ( $T_c \leq 114^{\circ}C$ )                                                     | $I_{T(RMS)}$ | 12      | A                |
| Non repetitive surge peak on-state current (full cycle , $t_p=20ms$ , $T_j=25^{\circ}C$ )            | $I_{TSM}$    | 120     | A                |
| Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$ , $T_j=25^{\circ}C$ )          |              | 132     |                  |
| $I^2t$ value for fusing ( $t_p=10ms$ , $T_j=25^{\circ}C$ )                                           | $I^2t$       | 72      | A <sup>2</sup> s |
| Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100Hz$ , $T_j=150^{\circ}C$ ) | $di/dt$      | 100     | A/ $\mu s$       |
| Peak gate current ( $t_p=20\mu s$ , $T_j=150^{\circ}C$ )                                             | $I_{GM}$     | 4       | A                |

|                                                                                     |             |     |    |
|-------------------------------------------------------------------------------------|-------------|-----|----|
| Average gate power dissipation ( $T_j=150^{\circ}\text{C}$ )                        | $P_{G(AV)}$ | 1   | W  |
| Peak gate power                                                                     | $P_{GM}$    | 10  | W  |
| Peak pulse voltage<br>( $T_j=25^{\circ}\text{C}$ ; non-repetitive, off-state; FIG ) | $V_{pp}$    | 4.5 | kV |

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^{\circ}\text{C}$  unless otherwise specified)

| Symbol      | Test Condition                                                                     | Quadrant    | Value |     | Unit             |
|-------------|------------------------------------------------------------------------------------|-------------|-------|-----|------------------|
| $I_{GT}$    | $V_D=12\text{V}$ $R_L=33\Omega$                                                    | I - II -III | MAX.  | 20  | mA               |
| $V_{GT}$    |                                                                                    | I - II -III | MAX.  | 1   | V                |
| $V_{GD}$    | $V_D=V_{DRM}$ $T_j=150^{\circ}\text{C}$<br>$R_L=3.3\text{k}\Omega$                 | I - II -III | MIN.  | 0.2 | V                |
| $I_L$       | $I_G=1.2I_{GT}$                                                                    | I -III      | MAX.  | 25  | mA               |
|             |                                                                                    | II          |       | 55  |                  |
| $I_H$       | $I_T=500\text{mA}$                                                                 |             | MAX.  | 25  | mA               |
| $dV/dt$     | $V_D=540\text{V}$ Gate Open $T_j=150^{\circ}\text{C}$                              |             | MIN.  | 400 | V/ $\mu\text{s}$ |
| $(dI/dt)_c$ | $(dV/dt)_c=20\text{V}/\mu\text{s}$ , $T_j=150^{\circ}\text{C}$                     |             | MIN.  | 3   | A/ms             |
| $t_{on}$    | $I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$<br>$T_j=25^{\circ}\text{C}$ |             | TYP.  | 3   | $\mu\text{s}$    |
| $t_{off}$   |                                                                                    |             |       | 60  |                  |

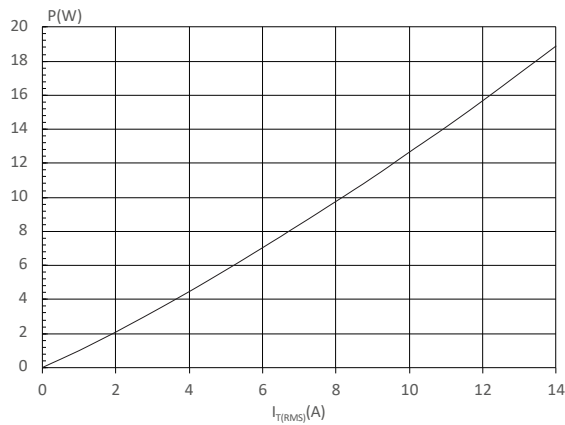
**STATIC CHARACTERISTICS**

| Symbol    | Parameter                                |                           | Value(MAX.) | Unit          |
|-----------|------------------------------------------|---------------------------|-------------|---------------|
| $V_{TM}$  | $I_{TM}=17\text{A}$ $t_p=380\mu\text{s}$ | $T_j=25^{\circ}\text{C}$  | 1.4         | V             |
| $V_{TO}$  | Threshold voltage                        | $T_j=150^{\circ}\text{C}$ | 0.75        | V             |
| $R_D$     | Dynamic resistance                       | $T_j=150^{\circ}\text{C}$ | 37          | m $\Omega$    |
| $I_{DRM}$ | $V_D=V_{DRM}$ $V_R=V_{RRM}$              | $T_j=25^{\circ}\text{C}$  | 5           | $\mu\text{A}$ |
| $I_{RRM}$ |                                          | $T_j=150^{\circ}\text{C}$ | 2           | mA            |

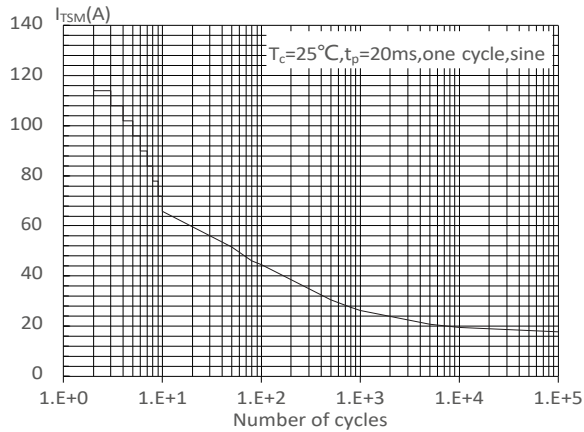
**THERMAL RESISTANCES**

| Symbol        | Parameter                | Value | Unit                        |
|---------------|--------------------------|-------|-----------------------------|
| $R_{th(j-c)}$ | junction to case (AC)    | 2.3   | $^{\circ}\text{C}/\text{W}$ |
| $R_{th(j-a)}$ | junction to ambient (AC) | 60    | $^{\circ}\text{C}/\text{W}$ |

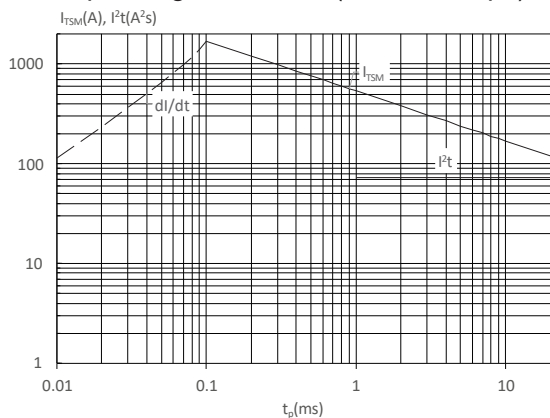
**FIG :** Maximum power dissipation versus RMS on-state current



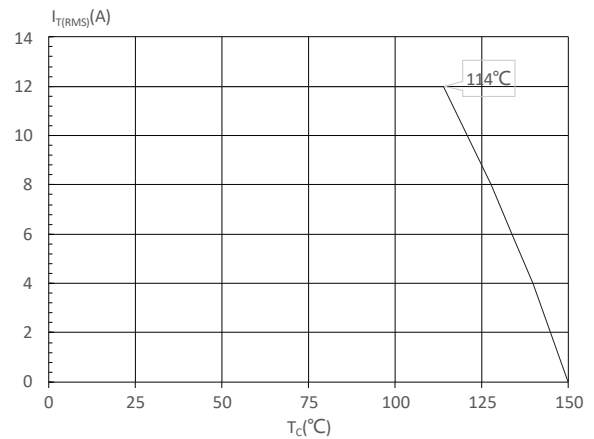
**FIG :** Surge peak on-state current versus number of cycles



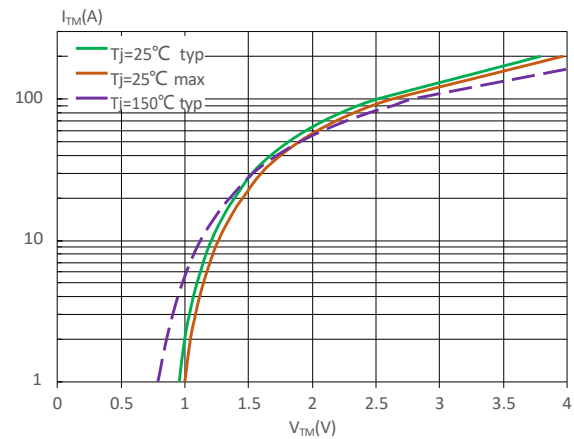
**FIG :** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 100\text{A}/\mu\text{s}$ )



**FIG :** RMS on-state current versus case temperature



**FIG :** On-state characteristics



**FIG :** Relative variations of gate trigger current, holding current and latching current versus junction temperature

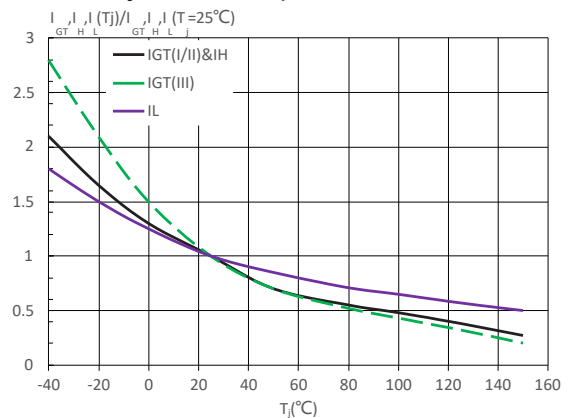
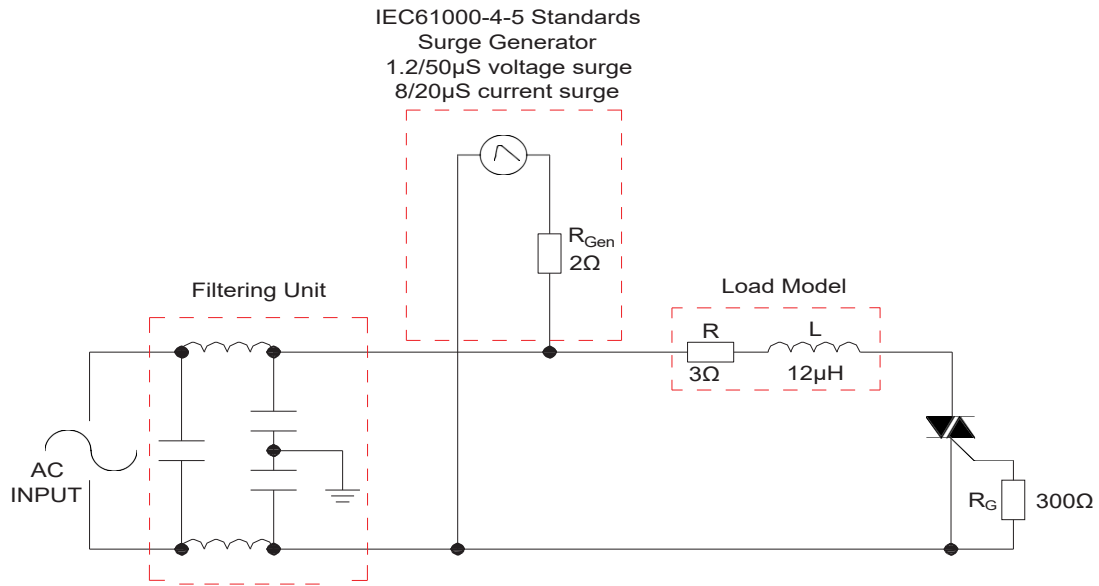


FIG : Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics